Amendments to the Specification

Please amend the paragraph beginning on page 1, line 12, as follows:

In recent years, a method of forming a sacrificial layer on a substrate such as a silicon wafer, forming a thin film structure patterned in a desired shaped on the sacrificial layer, and thereafter forming a desired three-dimensional structure by removing the sacrificial layer has been attracting ~~attentions~~attention. Since it is possible to form a large number of fine three-dimensional structures accurately and at a high density with this method, the method is suitable for manufacturing a spatial light modulation element and the like.

Please amend the paragraph beginning on page 1, line 22, as follows:

As a method of removing the sacrificial layer present between the substrate and the thin film structure in such a method of manufacturing a three-dimensional structure using a sacrificial layer, Japanese Patent Laid-open Publication No. 2001-13426 and Japanese Patent Laid-open Publication No. 2001-129798 disclose use of a solution for wet etching such as a hydrofluoric acid water solution. However, in the solution for etching like the hydrofluoric acid water solution that uses water as a solvent, a phenomenon in which water molecules adhere to the thin film structure at the time of etching and the thin film structure adheres to the substrate due to a surface tension of the water molecules tends to occur. When the fine thin film structure adheres to the substrate once, it is not easy to peel off the thin film structure. Thus, the thin film structure may keep adhering to the substrate after ~~a dry process to make~~drying, making it impossible to obtain a desired three-dimensional shape. In particular, when a thin film structure of a three-dimensional shape including a movable portion is formed, if the thin film structure adheres to a substrate, a function of the movable portion cannot be performed.

Please amend the paragraph beginning on page 18, line 6, as follows:

In a plasma ashing process, heat of reaction is generated by a reaction of the sacrificial layers 80 and 82 and the sacrificial layer 81 and the plasma. In particular, in the ineffective area 22, since the sacrificial layer 80 and the sacrificial layer 82 overlap directly, the reaction with the plasma quickly develops from the entire upper surface to the substrate 11. Thus, an ashing rate is high. Consequently, heat of reaction is generated suddenly in the ineffective area 22, and temperature of the ineffective area 22 rises. On the other hand, in the effective area 20 and the dummy area 21, since the displacement portion 13 and the dummy structure ~~13~~33 are sandwiched between the sacrificial layer 80 and the sacrificial layer 82, after the sacrificial layer 82 on the upper side is removed by the reaction with the plasma, the plasma reacts with the sacrificial layers 80 and 81 while gradually invading from gaps of the displacement portion 13 and the dummy structure 33. Thus, a reaction rate of the effective area 20 and the dummy area 21 is low compared with that of the ineffective area 22, and temperature of the effective area 20 and the dummy area 21 does not rise to high temperature like that of the ineffective area 22. When the inventors performed an experiment to check a temperature distribution of a substrate, as shown in Fig. 7(b), temperature of the ineffective area 22 rose to high temperature of several hundred degrees, which was higher than a substrate temperature at the time of formation of the Al films 73 and 72 and the SiN film 71 constituting the displacement portion 13. On the other hand, temperature of the effective area 20 and the dummy area 21 was lower than the substrate temperature at the time of formation of the films.